

2SC4500(L)/(S)

Silicon NPN Epitaxial

HITACHI

Application

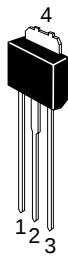
Low frequency amplifier

Outline

DPAK

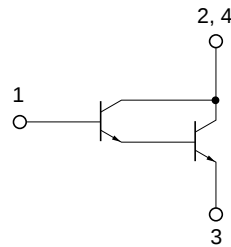


S Type



L Type

- 1. Base
- 2. Collector
- 3. Emitter
- 4. Collector



Absolute Maximum Ratings (Ta = 25°C)

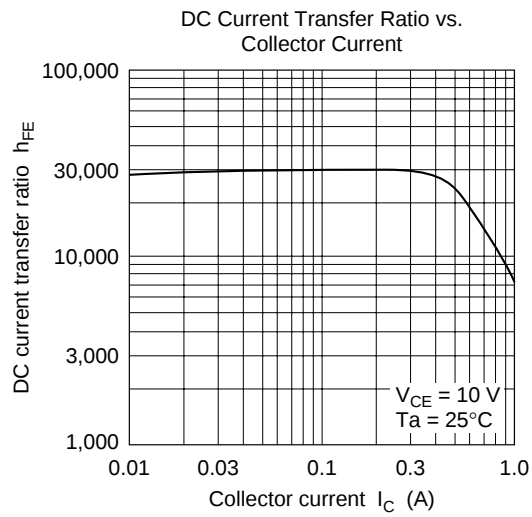
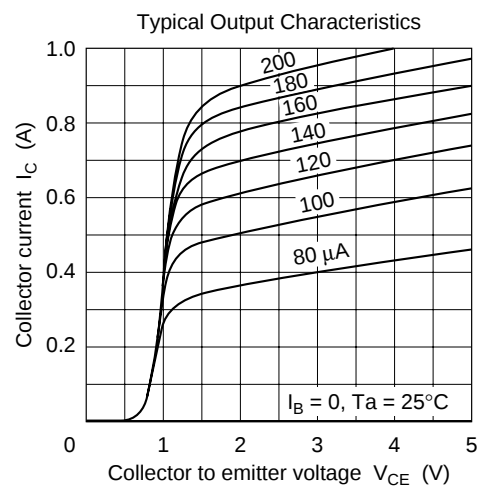
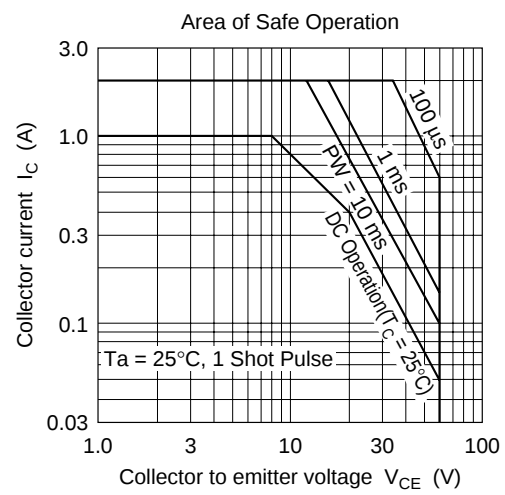
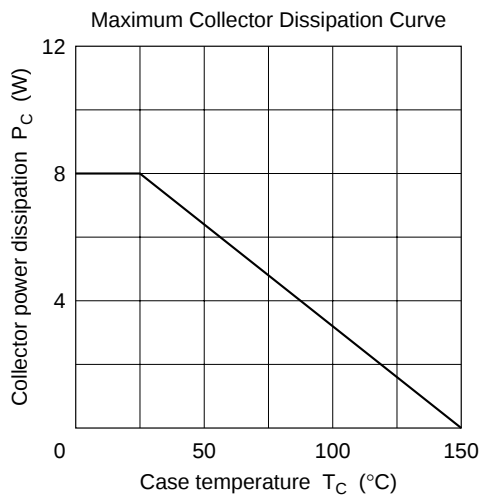
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	60	V
Collector to emitter voltage	V_{CEO}	60	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	1	A
Collector peak current	$I_{C\ (peak)}$	2	A
Collector power dissipation	P_C	0.8	W
	P_C^{*1}	8	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

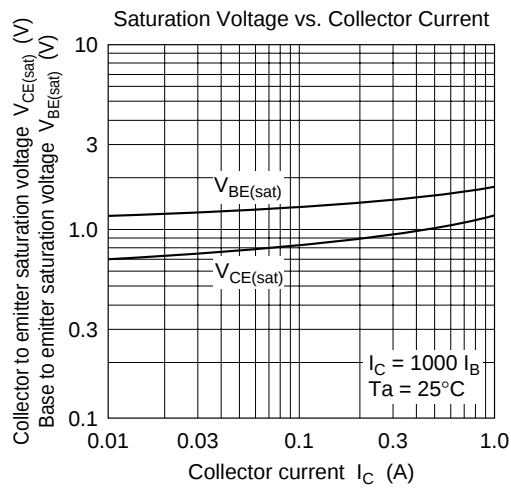
Note: 1. Value at $T_C = 25^{\circ}C$.

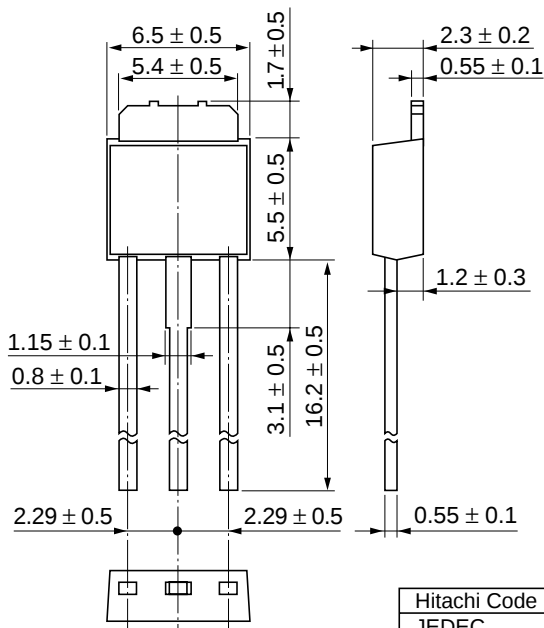
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	60	—	—	V	$I_C = 1\ mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 0.1\ mA, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB} = 60\ V, I_E = 0$
DC current transfer ratio	h_{FE}	2000	—	—		$V_{CE} = 10\ V, I_C = 500\ mA^{*1}$
Collector to emitter saturation voltage	$V_{CE\ (sat)}$	—	—	1.5	V	$I_C = 500\ mA, I_B = 0.5\ mA^{*1}$
Base to emitter saturation voltage	$V_{BE\ (sat)}$	—	—	2.0	V	$I_C = 500\ mA, I_B = 0.5\ mA^{*1}$
Turn on time	t_{on}	—	100	—	ns	$V_{CC} = 12\ V, I_C = 250\ mA,$
Turn off time	t_{off}	—	600	—	ns	$I_{B1} = -I_{B2} = 5\ mA$

Note: 1. Pulse Test.







Hitachi Code	DPAK (L)-(1)
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.42 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
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Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
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Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX
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